Panasonic

MOS FET

FCAB21490L1

FCAB21490L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Source-source ON resistance:RSS(on) typ. = 2.2 m Ω (VGS = 3.8 V)
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)

■ Marking Symbol: 7F

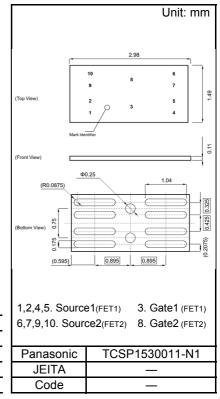
■ Packaging

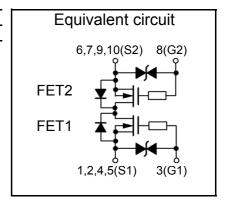
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

| Parameter | | Symbol | Rating | Unit | |
|---------------------------|----------|--------|-------------|------|--|
| Source-source Voltage | | VSS | 12 | V | |
| Gate-source Voltage | | VGS | ±8 | V | |
| Source Current | DC *1 | IS1 | 13.5 | Α | |
| | DC *2 | IS2 | 29 | Α | |
| | Pulse *3 | ISp | 135 | Α | |
| Total Power Dissipation | DC *1 | PD1 | 0.54 | W | |
| | DC *2 | PD2 | 3.5 | W | |
| Channel Temperature | | Tch | 150 | °C | |
| Storage Temperature Range | | Tsta | -55 to +150 | °C | |

- Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$) using the minimum recommended pad size ($36\mu\text{m}$ Copper).
 - *2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).
 - *3 $t = 10 \mu s$, Duty Cycle $\leq 1 \%$





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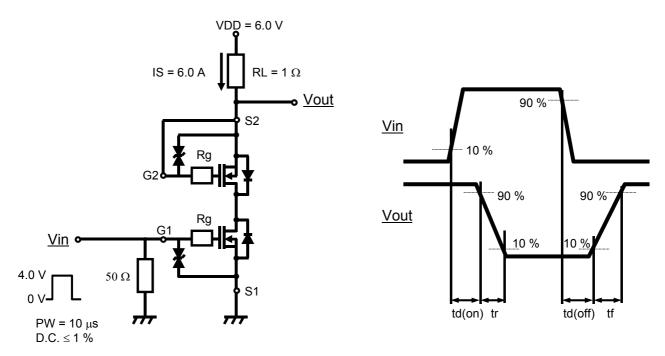
■ Electrical Characteristics Ta = 25 °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit | |
|-----------------------------------|----------|--|------|------|------|------|--|
| Source-source Breakdown Voltage | VSSS | IS = 1.0 mA, VGS = 0 V | 12 | | | V | |
| Zero Gate Voltage Source Current | ISSS | VSS = 12 V, VGS = 0 V | | | 1.0 | μА | |
| Gate-source Leakage Current | IGSS | $VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$ | | | ±10 | | |
| | | VGS = ±5 V, VSS = 0 V | | | ±1.0 | μΑ | |
| Gate-source Threshold Voltage | Vth | IS = 1.11 mA, VSS = 10 V | 0.35 | 0.90 | 1.4 | V | |
| Source-source On-state Resistance | RSS(on)1 | IS = 6.0 A, VGS = 4.5 V | 1.55 | 2.1 | 2.75 | mΩ | |
| | RSS(on)2 | IS = 6.0 A, VGS = 3.8 V | 1.6 | 2.2 | 2.85 | | |
| | RSS(on)3 | IS = 6.0 A, VGS = 3.1 V | 1.65 | 2.4 | 3.95 | | |
| | RSS(on)4 | IS = 6.0 A, VGS = 2.5 V | 1.9 | 3.1 | 6.1 | | |
| Body Diode Forward Voltage | VF(s-s) | IF = 6.0 A, VGS = 0 V | | 0.6 | 1.2 | V | |
| Input Capacitance *1 | Ciss | | | 3570 | | pF | |
| Output Capacitance *1 | Coss | VSS = 10 V, VGS = 0 V, f = 1 kHz | | 460 | | | |
| Reverse Transfer Capacitance *1 | Crss | | | 410 | | | |
| Turn-on delay Time *1,*2 | td(on) | VDD = 6.0 V, VGS = 0 to 4.0 V | | 0.7 | | μS | |
| Rise Time *1,*2 | tr | IS = 6.0 A | | 1.5 | | | |
| Turn-off delay Time *1,*2 | td(off) | VDD = 6.0 V, VGS = 4.0 to 0 V | | 6.7 | | μS | |
| Fall Time *1,*2 | tf | IS = 6.0 A | | 4.1 | | | |
| Total Gate Charge *1 | Qg | VDD = 6.0 V | | 25 | | | |
| Gate-source Charge *1 | Qgs | VGS = 0 to 4.0 V, | | 12 | | nC | |
| Gate-drain Charge *1 | Qgd | IS = 6.0 A | | 6 | | | |

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2:Measurement circuit

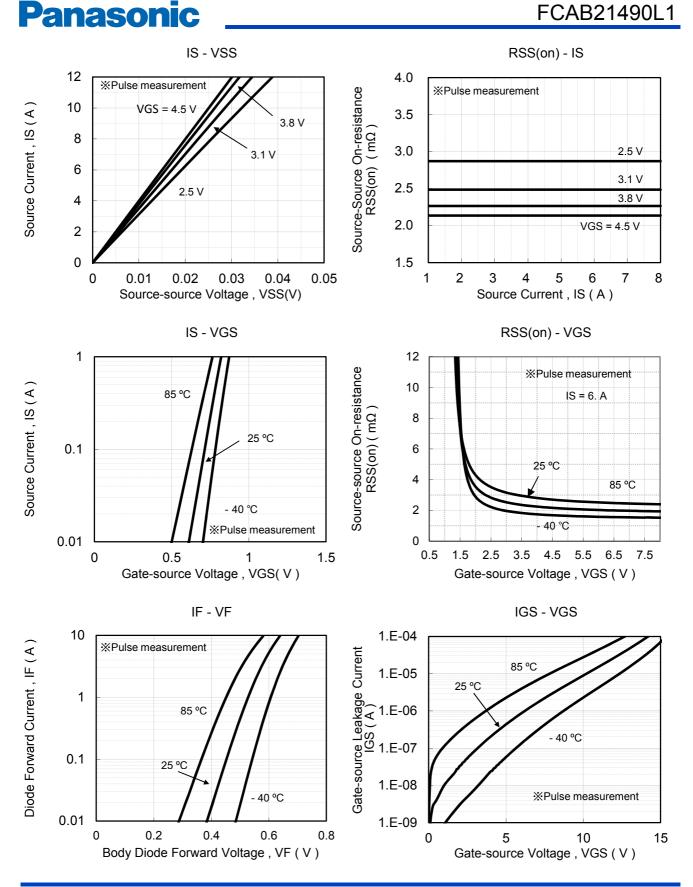


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Dynamic Input / Output Characteristics

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ISS - VSS

1.E-03 4.0 Zero Gate Voltage Source Current Gate-source Voltage, VGS (V) VDD = 6.0 V **XPulse** measurement IS = 6.0 A1.E-04 3.0 1.E-05 85 °C (A) 1.E-06 (S) 1.E-07 2.0 25 °C 1.E-08 1.0 1.E-09 40 °C 1.E-10 0.0 0 5 10 15 20 5 0 10 20 25 15 30 Source-source Voltage, VSS (V) Gate Charge, Qg (nC) Rth - tsw Safe Operating Area Thermal Resistance , Rth (°C / W) 1000 1000 limited by RSS(on) (VGS = 3.8 V) (A) Absolute Maximum Source Current, IS (A) 100 100 - 1 ms 3 ms 10 (B) 11 ms 10 100 ms 1 1 s DC 1 Ta = 25 °C, Mounted on FR4 board 0.1 ed on FR4 board (25.4 mm×25.4 mm×t1.0 mm). (25.4 mm \times 25.4 mm \times t1.0 mm). using the minimum recommended pad size(36 μ m Copper) . using the minimum recommended pad size (36 µm Copper)

(B) Mounted on Ceramic substrate (70 mm × 70 mm × t1 0 mm). 0.01 0.1 100 0.1 10 0.001 0.01 1000 0.1 1 10 100 Pulse Width, tsw (s) Source-source Voltage, VSS (V) Normalized Effective Transient Thermal Impedance Thermal Response 10 Mounted on FR4 board (25.4 mm×25.4 mm×t1.0 mm). using the minimum recommended pad size(36 μm Copper) 1 0.2 0.1 0.05 0.1 0.02 0.01 0.001 0.0001 0.001 0.01 0.1 100 1000 Square Wave Pulse Duration (s)

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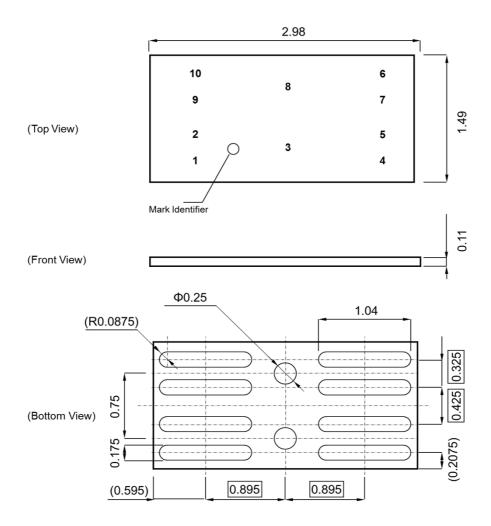
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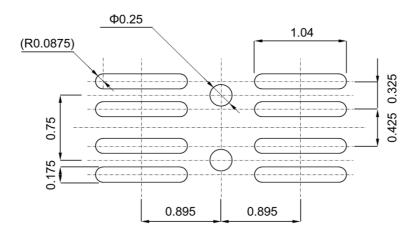
■ Outline

Unit: mm



■ Land Pattern (Reference)

Unit: mm



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